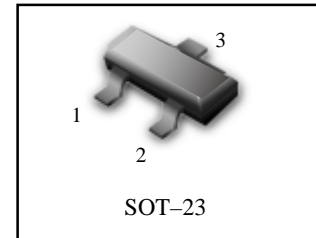


# General Purpose Transistors

## NPN Silicon

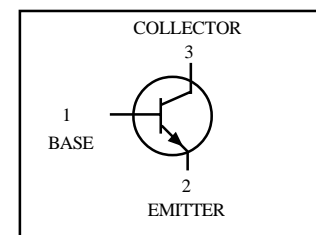
### FEATURE

- High current capacity in compact package.  
 $I_C = 1.5A$ .
- Epitaxial planar type.
- PNP complement: FTA8550H
- Pb-Free Package is available.



### DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
FTC8050H	1FC	3000/Tape&Reel



### MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Collector-Emitter Voltag	$V_{CE0}$	25	V
Collector-Base Voltag	$V_{CBO}$	40	V
Emitter-Base Voltag	$V_{EBO}$	5	V
Collector Current-continuou	$I_C$	1500	mAdc

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,(1) $T_A = 25^\circ C$ Derate above $25^\circ C$	$P_D$	225 18	mW mW/ C
Thermal Resistance,Junction to Ambient	$R\theta_{JA}$	556	C/W
Total Device Dissipation Alumina Substrate,(2) $T_A = 25^\circ C$ Derate above $25^\circ C$	$P_D$	300 24	mW mW/ C
Thermal Resistance,Junction to Ambient	$R\theta_{JA}$	417	C/W
Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +150	C



# FTC8050H

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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## OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ( $I_C = 1.0\text{mA}$ )	$V_{(BR)CEO}$	25	-	-	V
Emitter-Base Breakdown Voltage ( $I_E = 100\mu\text{A}$ )	$V_{(BR)EBO}$	5	-	-	V
Collector-Base Breakdown Voltage ( $I_C = 100\mu\text{A}$ )	$V_{(BR)CBO}$	40	-	-	V
Collector Cutoff Current ( $V_{CB} = 35\text{V}$ )	$I_{CBO}$	-	-	150	nA
Emitter Cutoff Current ( $V_{EB} = 4\text{V}$ )	$I_{EBO}$	-	-	150	nA

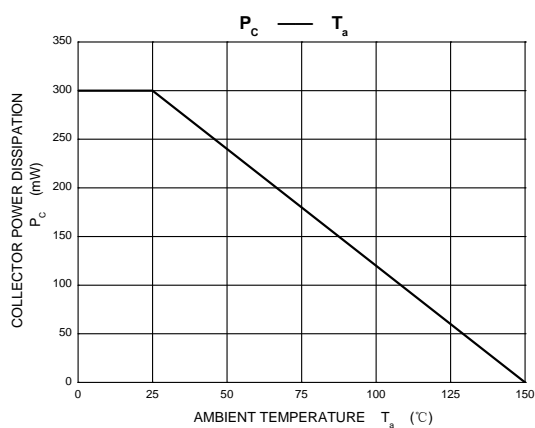
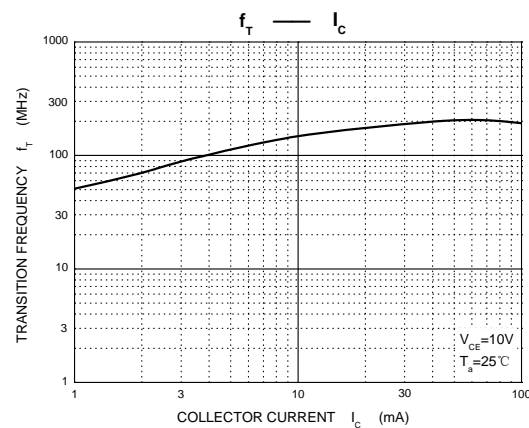
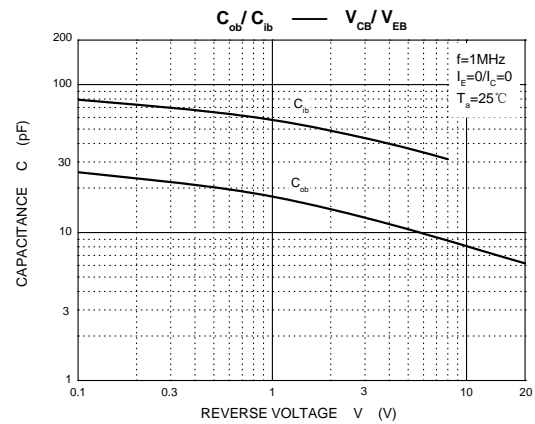
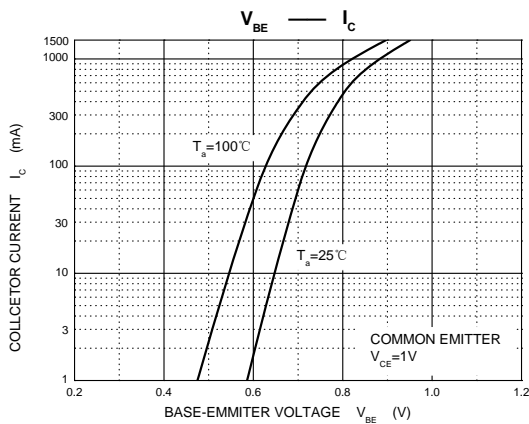
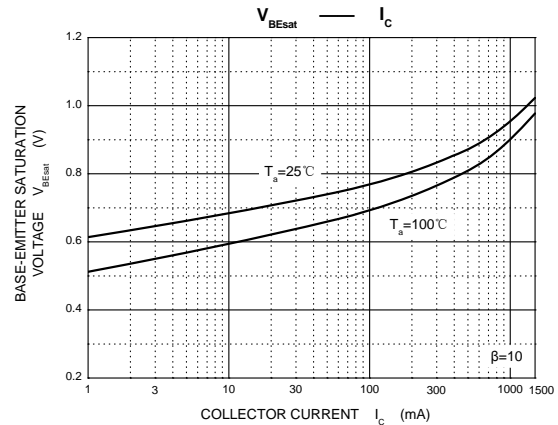
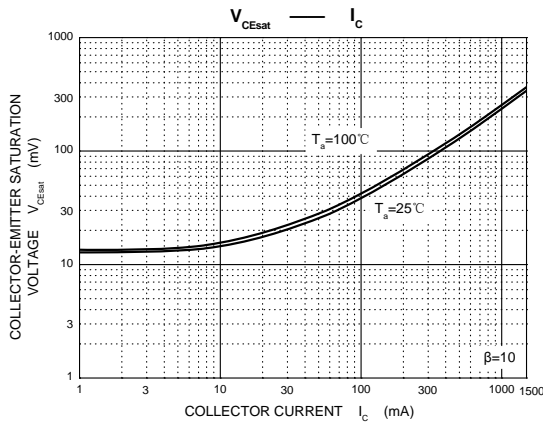
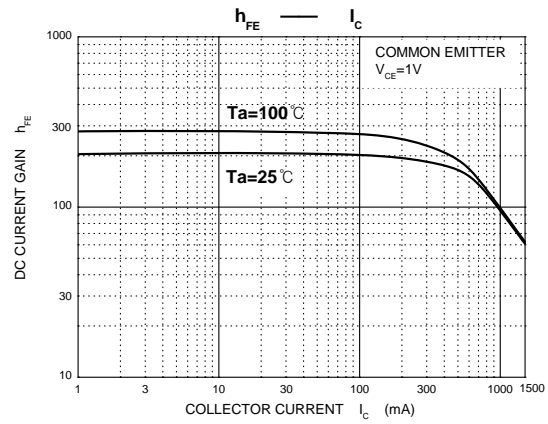
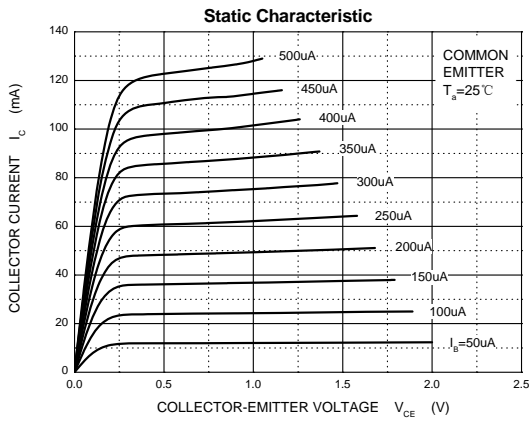
## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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## ON CHARACTERISTICS

DC Current Gain $I_C = 100\text{mA}, V_{CE} = 1\text{V}$	$h_{FE}$	150	-	300	
Collector-Emitter Saturation Voltage ( $I_C = 800\text{mA}, I_B = 80\text{mA}$ )	$V_{CE(S)}$	-	-	0.5	V

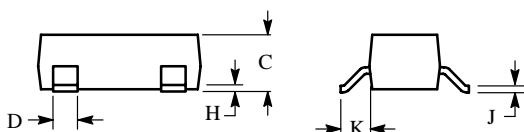
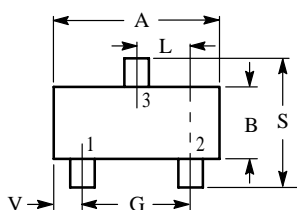
## Typical Characteristics



## SOT-23

### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982
2. CONTROLLING DIMENSION: INCH.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

PIN 1 BASE  
 2 EMITTER  
 3 COLLECTOR

